

Rare-Earth Cobalt Gallides $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (RE = Gd–Er, Y): Self-Interstitial Derivatives of RE_2CoGa_8

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Dedicated to Professor John D. Corbett on the occasion of his 85th birthday

Keywords: Rare earths / Cobalt / Gallium / Intermetallic phases / Magnetic properties

Ternary rare-earth cobalt gallides $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (RE = Gd–Er, Y) have been prepared by arc-melting of the elements followed by annealing at 800 °C. Single crystals of the Gd and Tb members were also grown in the presence of a Ga self-flux. They extend the rare-earth substitution possible in the $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$ -type structure (Pearson symbol $tP23$, space group $P4/mmm$, $Z = 1$), in which additional Co atoms enter as self-interstitials into the parent RE_2CoGa_8 structure. Structural refinements were carried out on single-crystal (RE = Gd, Tb) and powder (RE = Dy, Ho, Er, Y) X-ray diffraction data. Cell parameters lie in the ranges of $a = 6.03$ – 5.96 Å and $c =$

11.11 – 10.96 Å. Magnetic measurements on $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (RE = Gd, Tb, Dy) reveal that they order antiferromagnetically below T_N of 19, 25, and 14 K, respectively; $\text{Y}_4\text{Co}_3\text{Ga}_{16}$ is Pauli paramagnetic. The electrical resistivity of $\text{Tb}_4\text{Co}_3\text{Ga}_{16}$ undergoes a transition coincident with the magnetic ordering temperature. Band structure calculations on $\text{Y}_4\text{Co}_3\text{Ga}_{16}$ indicate that the major bonding contributions arise from Co–Ga and Ga–Ga interactions, with the stuffing of interstitial Co atoms into octahedral sites of the parent Y_2CoGa_8 structure, which provides additional Co–Ga bonding stabilization.

Introduction

An emerging series of ternary intermetallic gallides and indides with tetragonal structures can be described by the general formula $\text{RE}_n\text{M}_m\text{X}_{3n+2m}$ (RE = rare-earth metal, mostly Ce and Yb; M = Co, Rh, Ir; X = Ga, In), in which the indices n and m refer to the number of AuCu_3 -type and PtHg_2 -type slabs, respectively, that are condensed together.^[1–3] Although many hypothetical structures can be generated in this manner, CePt_2In_7 remains the only compound known with $n = 1$ and $m = 2$.^[4] All other real examples are restricted to $n = 1, 2$ and $m = 1$; the general formula then simplifies to $\text{RE}_n\text{MX}_{3n+2}$. These compounds, especially CeCoIn_5 ,^[5] have elicited considerable interest as heavy fermion materials and unconventional superconductors.^[6–14] The $n = 1$ members, which are numerous, include the actinide superconductor PuCoGa_5 ($T_c = 18$ K),^[15,16] the $n = 2$ members exhibit predominantly antiferromagnetic ordering and some also show superconductivity, such as Ce_2CoIn_8 ($T_c = 0.4$ K).^[17] Among the rare-earth cobalt gallides $\text{RE}_n\text{CoGa}_{3n+2}$, previous magnetic studies have led to the observation that both the antiferromagnetic ordering tem-

peratures and superconducting critical temperatures tend to decrease on proceeding from RECoGa_5 to RE_2CoGa_8 .^[8,11] Given these trends, an ongoing goal in these studies is to seek an understanding of how the physical properties correlate with, among other factors, the crystal structures, which are built up from such recognizable slabs.

In the course of investigating the Sm–Co–Ga system (motivated by the chemical similarity of Sm to Pu), Jia et al. recently discovered the superconducting compound $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$ ($T_c = 2.8$ K).^[18] This result highlights the possibility for further structural variation not evident from the formula $\text{RE}_n\text{MX}_{3n+2}$. The structure of $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$ is derived by stuffing additional Co atoms into available octahedral sites within pairs of REGa_3 slabs of RE_2CoGa_8 (or “ $\text{RE}_4\text{Co}_2\text{Ga}_{16}$ ”). Herein we explore the extent of RE substitution in the $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$ structure, clarify the bonding with the aid of band structure calculations and examine the magnetic properties of some of these analogues.

Results and Discussion

Crystal Structure

The preparation of $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ underscores the richness of the RE–Co–Ga systems, which already comprise many ternary intermetallic compounds.^[19] The previously unique structure of $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$ ^[18] has now been extended

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Supporting information for this article is available on the WWW under <http://dx.doi.org/10.1002/ejic.201100283>.

to include representatives with the smaller RE metals (Gd–Er, Y); the cell parameters vary smoothly in this series (Figure 1). Synthesis of these compounds (through reaction of the elements by arc-melting followed by annealing at 800 °C) becomes more difficult with smaller RE elements, for which the samples contain other phases such as RE₂CoGa₈ with a closely related structure.^[1] Crystals of RE₄Co₃Ga₁₆ and RE₂CoGa₈ are impossible to distinguish visually except by full single-crystal X-ray diffraction analysis. Fortunately, the Gd and Tb members could be obtained as single crystals through use of excess Ga as a self-flux. For the remaining members, powder X-ray diffraction data were refined with the Rietveld method. A representative fit to the diffraction pattern is shown for Dy₄Co₃Ga₁₆ in Figure 2; fits for the other compounds are available in Figure S1 in Supporting Information. Crystallographic data for all six compounds are summarized in Table 4, final values of the positional and displacement parameters are given in Table 1 and interatomic distances are given in Table 2.

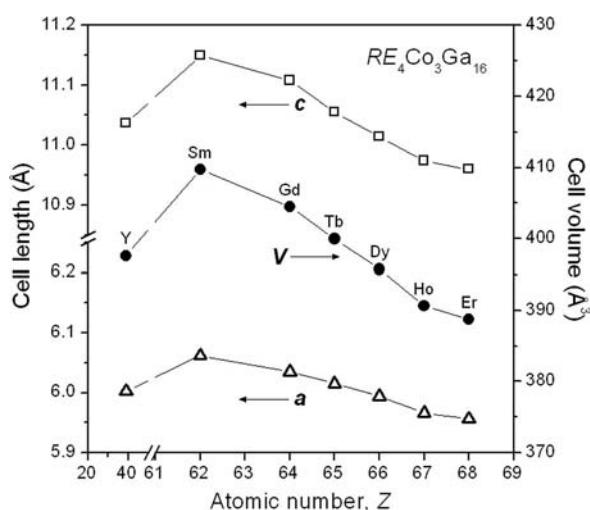


Figure 1. Plot of cell parameters for RE₄Co₃Ga₁₆.

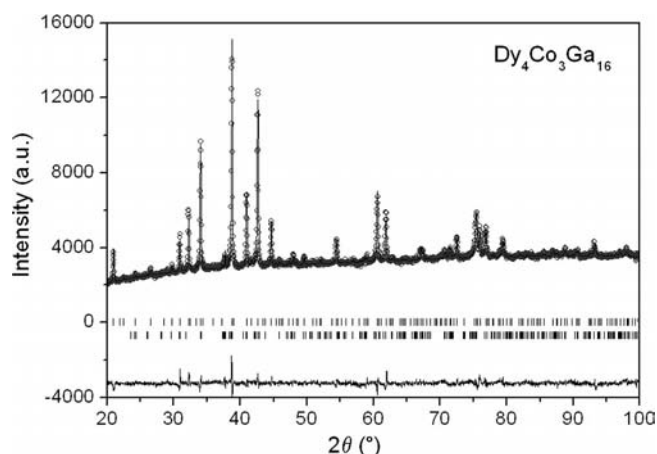


Figure 2. Rietveld refinement results for Dy₄Co₃Ga₁₆. The observed profile is indicated by circles and the calculated profile by the solid line. Bragg peak positions are located by the upper set of vertical tick marks; the lower set corresponds to small amounts (ca. 4%) of Dy₂Co₃Ga₉. The difference plot is shown at the bottom.

A $\sqrt{2}a \times \sqrt{2}a$ superstructure develops on proceeding from RE₂CoGa₈ to RE₄Co₃Ga₁₆. The *c/a* ratio in the RE₂CoGa₈ (RE = Sm, Gd–Tm, Lu, Y) series has a constant value of 2.61,^[1,11] essentially identical to the $\sqrt{2}(c/a)$ ratio of $\sqrt{2} \times 1.84 = 2.60$ in the RE₄Co₃Ga₁₆ series (RE = Sm, Gd–Er, Y). Although the structure of RE₄Co₃Ga₁₆ is derived by stuffing Co atoms into the structure of RE₂CoGa₈, analysis

Table 1. Atomic coordinates and equivalent isotropic displacement parameters for RE₄Co₃Ga₁₆ (RE = Gd–Er, Y).^[a]

	Gd ₄ Co ₃ Ga ₁₆	Tb ₄ Co ₃ Ga ₁₆	Dy ₄ Co ₃ Ga ₁₆	Ho ₄ Co ₃ Ga ₁₆	Er ₄ Co ₃ Ga ₁₆	Y ₄ Co ₃ Ga ₁₆
RE at 4i (0, 1/2, z)						
z	0.19427(3)	0.19396(4)	0.1935(3)	0.1927(3)	0.1939(3)	0.1959(4)
U _{eq} or U _{iso} (Å ²)	0.0067(2)	0.0066(2)	0.015(2)	0.024(2)	0.007(2)	0.011(2)
Co1 at 2e (0, 1/2, 1/2)						
U _{eq} or U _{iso} (Å ²)	0.0072(3)	0.0069(4)	0.006(3)	0.004(3)	0.006(3)	0.036(4)
Co2 at 1a (0, 0, 0)						
U _{eq} or U _{iso} (Å ²)	0.0117(5)	0.0124(5)	0.006(3)	0.004(3)	0.006(3)	0.036(4)
Ga1 at 8r (x, x, z)						
x	0.24999(8)	0.25016(9)	0.252(1)	0.251(1)	0.251(2)	0.251(1)
z	0.38505(7)	0.38431(8)	0.3836(3)	0.3825(3)	0.3835(3)	0.3821(3)
U _{eq} or U _{iso} (Å ²)	0.0103(2)	0.0096(2)	0.011(1)	0.020(1)	0.016(2)	0.015(1)
Ga2 at 4j (x, x, 0)						
x	0.2809(1)	0.2805(2)	0.282(1)	0.273(1)	0.272(2)	0.283(1)
U _{eq} or U _{iso} (Å ²)	0.0102(2)	0.0104(2)	0.011(1)	0.020(1)	0.016(2)	0.015(1)
Ga3 at 2h (1/2, 1/2, z)						
z	0.1952(1)	0.1954(2)	0.201(1)	0.211(2)	0.206(2)	0.200(1)
U _{eq} or U _{iso} (Å ²)	0.0099(3)	0.0090(3)	0.011(1)	0.020(1)	0.016(2)	0.015(1)
Ga4 at 2g (0, 0, z)						
z	0.2194(1)	0.2190(2)	0.223(1)	0.213(2)	0.214(2)	0.222(1)
U _{eq} or U _{iso} (Å ²)	0.0101(3)	0.0101(3)	0.011(1)	0.020(1)	0.016(2)	0.015(1)

[a] U_{eq}, defined as one-third of the trace of the orthogonalized U_{ij} tensor, applies to results from single-crystal data (RE = Gd, Tb); U_{iso} applies to results from powder Rietveld refinements (RE = Dy, Ho, Er, Y).

Table 2. Selected interatomic distances (Å) in RE₄Co₃Ga₁₆ (RE = Gd–Er, Y).

	Gd ₄ Co ₃ Ga ₁₆	Tb ₄ Co ₃ Ga ₁₆	Dy ₄ Co ₃ Ga ₁₆	Ho ₄ Co ₃ Ga ₁₆	Er ₄ Co ₃ Ga ₁₆	Y ₄ Co ₃ Ga ₁₆
RE–Ga1 (×4)	3.0071(6)	2.9917(7)	2.979(5)	2.964(6)	2.958(8)	2.954(5)
RE–Ga3 (×2)	3.0174(3)	3.0074(2)	2.998(1)	2.990(1)	2.981(1)	3.001(1)
RE–Ga4 (×2)	3.0302(3)	3.0200(3)	3.015(1)	2.991(1)	2.986(2)	3.015(1)
RE–Ga2 (×4)	3.0460(3)	3.0311(4)	3.018(5)	2.993(6)	2.997(7)	3.042(5)
Co1–Ga1 (×8)	2.4865(4)	2.4815(5)	2.477(5)	2.472(6)	2.463(8)	2.489(4)
Co2–Ga2 (×4)	2.397(1)	2.386(1)	2.39(1)	2.31(1)	2.29(1)	2.401(5)
Co2–Ga4 (×2)	2.436(2)	2.421(2)	2.46(1)	2.34(2)	2.34(2)	2.46(1)
Ga1–Co1 (×2)	2.4865(4)	2.4815(5)	2.477(5)	2.472(6)	2.463(8)	2.489(4)
Ga1–Ga1	2.554(2)	2.558(2)	2.564(5)	2.579(5)	2.554(5)	2.602(5)
Ga1–Ga4	2.818(1)	2.805(2)	2.77(1)	2.82(1)	2.81(2)	2.76(1)
Ga1–Ga3	3.000(1)	2.980(1)	2.91(1)	2.82(1)	2.86(2)	2.91(1)
Ga1–Ga1 (×2)	3.017(1)	3.005(1)	2.98(1)	2.97(1)	2.97(1)	2.99(1)
Ga1–Ga1 (×2)	3.018(1)	3.009(1)	3.02(1)	2.99(1)	2.98(1)	3.01(1)
Ga2–Co2	2.397(1)	2.386(1)	2.39(1)	2.31(1)	2.29(1)	2.401(5)
Ga2–Ga2 (×2)	2.645(2)	2.640(2)	2.62(1)	2.70(1)	2.71(1)	2.61(1)
Ga2–Ga3 (×2)	2.863(1)	2.855(2)	2.89(1)	3.00(2)	2.96(2)	2.88(1)
Ga3–Ga2 (×4)	2.863(1)	2.855(2)	2.89(1)	3.00(2)	2.96(2)	2.88(1)
Ga3–Ga1 (×4)	3.000(1)	2.980(1)	2.91(1)	2.82(1)	2.86(2)	2.91(1)
Ga4–Co2	2.436(2)	2.421(2)	2.46(1)	2.34(2)	2.34(2)	2.46(1)
Ga4–Ga1 (×4)	2.818(1)	2.805(2)	2.77(1)	2.82(1)	2.81(2)	2.76(1)

of numerous crystals provides no evidence for the occurrence of nonstoichiometry in which Co atoms partially occupy the interstitial sites, i.e. RE₄Co_{2+x}Ga₁₆ ($0 < x < 1$). The parent RE₂CoGa₈ structure is built up of pairs of AuCu₃-type slabs alternating with PtHg₂-type slabs stacked along the *c* direction, $\frac{2}{3}$ [REGa₃] + $\frac{2}{3}$ [REGa₃] + $\frac{2}{3}$ [CoGa₂], with RE atoms in cuboctahedral (CN12) and Co atoms in cubic (CN8) coordination environments of the Ga atoms. The condensation of two [REGa₃] slabs leads to octahedral Ga₆ clusters that are empty in RE₂CoGa₈, but *half* of which are centred by additional Co atoms (CN6) in RE₄Co₃Ga₁₆ (Figure 3). Occupation of *all* these sites is precluded by the generation of Co–Ga distances that would be too short (2.1–2.3 Å) relative to the sum of the metallic radii (Pauling *R*₁ values of 1.16 Å for Co and 1.25 Å for Ga).^[20] Instead, the filled Ga₆ clusters expand to accommodate more reasonable Co–Ga distances of 2.3–2.4 Å (comparable to typical values such as those found in CoGa₃).^[21] whereas the empty Ga₆ clusters shrink considerably such that the centre-to-vertex distances become 1.9–2.2 Å [the shortest Co–Ga distance found in the literature is 2.195(4) Å in YCoGa₃Ge].^[22] The constraint that the Co–Ga distances within these clusters do not become shorter than ca. 2.3 Å sets the limit of substitution with the smallest RE metal to Er₄Co₃Ga₁₆, even though the parent RE₂CoGa₈ structure extends all the way to the Lu member.^[1,11] On the other hand, it might be thought that expansion of the structure by substitution with a larger RE metal should not be limited. For this consideration, it is important to note that the RE-centred cuboctahedra (in the AuCu₃-type slabs) share a common square face of Ga atoms with the Co-centred cubes (in the PtHg₂-type slabs). Because the PtHg₂-type slabs remain unperturbed on proceeding from RE₂CoGa₈ to RE₄Co₃Ga₁₆, the limit of substitution with the largest RE metal is the same for both series, at the Sm member. Within the range of RE substitution, the Ga–Ga distances within these squares (3.0 Å) match well with the RE–Ga

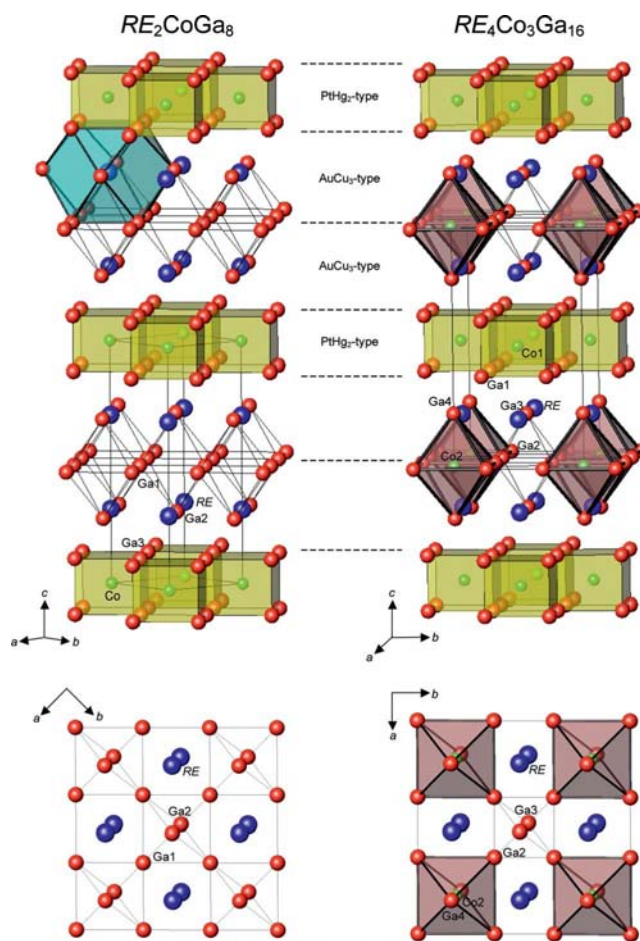


Figure 3. Comparison of RE₂CoGa₈ (RE = Sm, Gd–Tm, Lu, Y) and RE₄Co₃Ga₁₆ (RE = Sm, Gd–Er, Y) structures built up from AuCu₃- and PtHg₂-type slabs. The Co-centred cubes, as well as one of the RE-centred cuboctahedra, are highlighted in RE₂CoGa₈. Half of the formerly empty octahedral Ga₆ clusters in RE₂CoGa₈ are filled by additional Co atoms to form the structure of RE₄Co₃Ga₁₆.

distances (3.0 Å) to minimize distortion of the cub-octahedra. The Ga–Ga distances within the expanded Ga_6 clusters are longer (3.2–3.4 Å) and are nonbonding.

Properties

Measurements of the magnetic susceptibility reveal antiferromagnetic ordering at low temperatures for $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (RE = Gd, Tb, Dy) and temperature-independent Pauli paramagnetism for $\text{Y}_4\text{Co}_3\text{Ga}_{16}$ (Figure 4). For the Gd, Tb and Dy members, the inverse magnetic susceptibility was fitted to the Curie–Weiss law, $\chi = C/(T - \theta_p)$, in the linear portion of the high-temperature paramagnetic regime, and yielded the parameters listed in Table 3. The effective magnetic moments (derived from the Curie constants, C) slightly exceed the theoretical free-ion values for RE^{3+} species, but caution should be exercised because the samples contained small amounts of other phases which are magnetic (Figure S2 in Supporting Information). For example, the $\text{Tb}_4\text{Co}_3\text{Ga}_{16}$ sample contained ca. 3.5% by mass of $\text{Tb}_2\text{Co}_3\text{Ga}_9$.^[23] In principle, it should be possible to subtract the contribution of these other phases from the total magnetic susceptibility, but unfortunately the magnetic properties of $\text{RE}_2\text{Co}_3\text{Ga}_9$ phases are unknown.^[23] The con-

tamination of the $\text{Dy}_4\text{Co}_3\text{Ga}_{16}$ sample with minor amounts of both DyCoGa_5 and $\text{Dy}_2\text{Co}_3\text{Ga}_9$ is probably responsible for the high effective magnetic moment observed. Alternatively, the elevated magnetic moments may be intrinsic to the compounds, possibly from the contribution of Co atoms. However, this explanation is unlikely because $\text{Y}_4\text{Co}_3\text{Ga}_{16}$, which contains a non-magnetic RE^{3+} ion, is Pauli paramagnetic (Figure 4d).

The magnetic behaviour of $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ closely resembles that of the RE_2CoGa_8 phases, which also order antiferromagnetically at low temperatures.^[10–14] The general trend is that the Néel temperatures, T_N , decrease on proceeding from RE_2CoGa_8 (20, 28 and 18 K)^[11] to $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (19, 25 and 14 K) for the Gd, Tb and Dy members, respectively. Typical for ternary gallides or indides with related structures, such as those described in the introduction, RKKY interactions are assumed to be operative between the RE atoms. The values for T_N for $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ roughly follow de Gennes scaling, with similar deviations seen for the Tb and Dy members as for the RE_2CoGa_8 series.^[11] Many of the interesting metamagnetic transitions, characterized by steplike features seen in the isothermal magnetization curves for Tb_2CoGa_8 and Dy_2CoGa_8 ,^[11] become much less pronounced or disappear al-

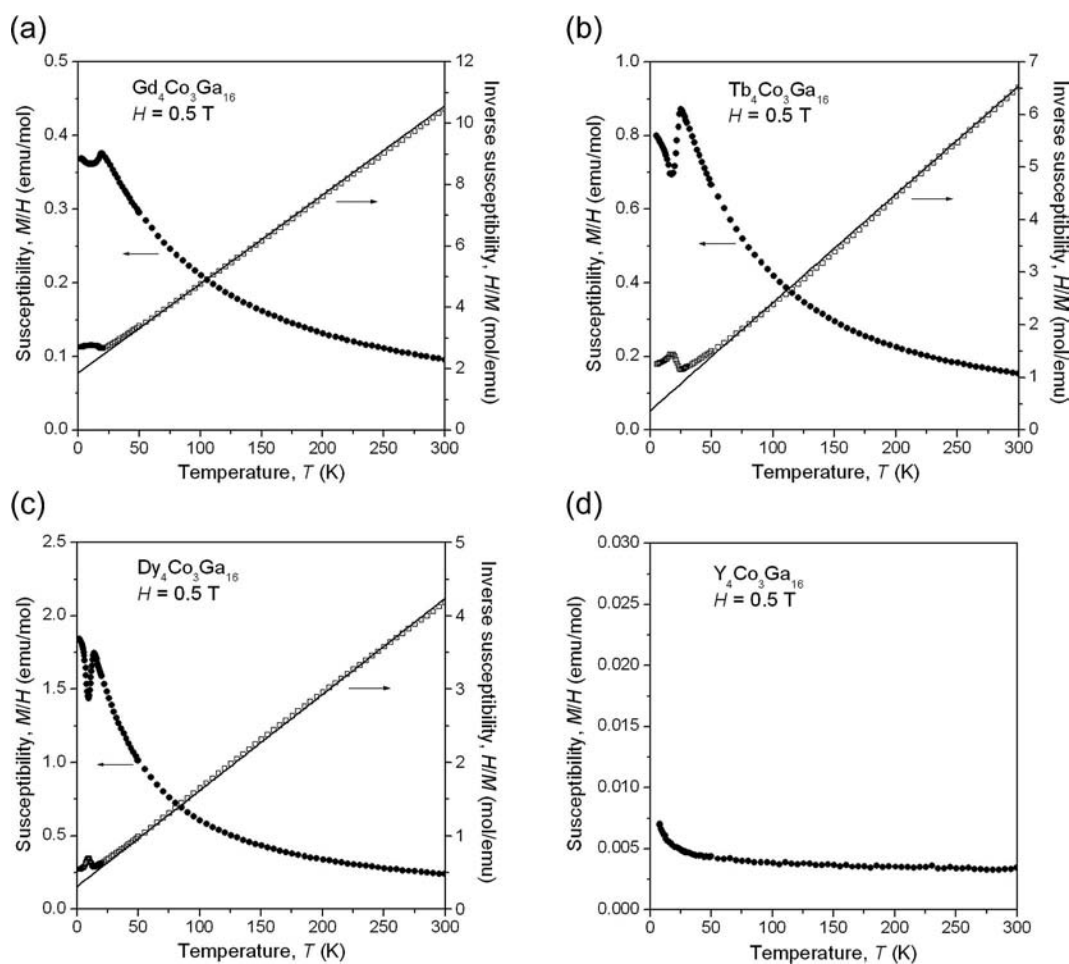


Figure 4. Zero-field-cooled dc magnetic susceptibility for $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ (RE = Gd, Tb, Dy, Y). For the Gd, Tb and Dy members, the inverse susceptibility is also shown, fitted to the Curie–Weiss law.

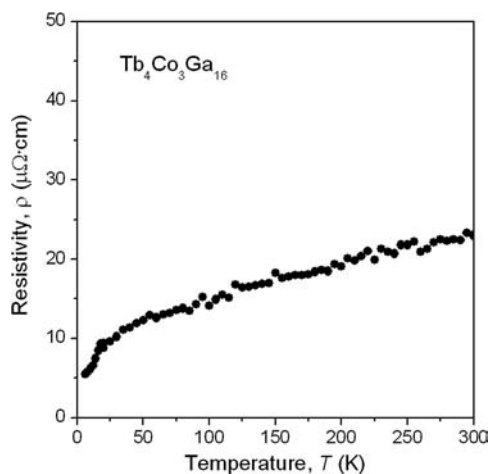
Table 3. Summary of magnetic data for RE₄Co₃Ga₁₆ (RE = Sm, Gd, Tb, Dy, Y).

Compound	Behaviour	T_N (K)	θ_p (K)	$\mu_{\text{eff, meas}}$ (μ_B/RE)	$\mu_{\text{eff, theor}}$ for RE ³⁺ (μ_B)
Sm ₄ Co ₃ Ga ₁₆ ^[a]	paramagnetic above 3.5 K			0.68	0.84
Gd ₄ Co ₃ Ga ₁₆	antiferromagnetic	19	−65(1)	8.30(2)	7.94
Tb ₄ Co ₃ Ga ₁₆	antiferromagnetic	25	−18(1)	9.85(2)	9.72
Dy ₄ Co ₃ Ga ₁₆	antiferromagnetic	14	−24(1)	12.36(2)	10.64
Y ₄ Co ₃ Ga ₁₆	Pauli paramagnetic				0

[a] Ref.^[18] The measured value of μ_{eff} for Sm₄Co₃Ga₁₆ is 1.36 $\mu_B/\text{f.u.}$ or 0.68 μ_B/Sm (not 0.34 μ_B/Sm as erroneously reported because μ_{eff} must be divided by the square root of the number of Sm atoms).

together in the corresponding Tb₄Co₃Ga₁₆ and Dy₄Co₃Ga₁₆ compounds (Figure S3 in Supporting Information). This observation supports the proposal that crystalline electric field (CEF) effects experienced by the Tb or Dy atoms are responsible for the deviation in T_N from de Gennes scaling,^[11] since the cuboctahedral coordination environment of Ga atoms around the RE atoms is distorted by the insertion of the interstitial Co₂ atoms into the parent RE₂CoGa₈ structure to form RE₄Co₃Ga₁₆.

The electrical resistivity of a single-crystal sample of one member, Tb₄Co₃Ga₁₆, was measured (Figure 5). As the temperature is lowered, the resistivity decreases in a relatively linear fashion. This is followed by a more rapid drop below a kink at 25 K, which coincides with T_N in the magnetic susceptibility curve, consistent with the loss of spin-disorder scattering upon the onset of antiferromagnetic ordering. The behaviour is similar to that seen for Tb₂CoGa₈ and other RE₂CoGa₈ compounds.^[10–12] No superconducting transition could be detected down to ca. 5 K.

Figure 5. Electrical resistivity of Tb₄Co₃Ga₁₆ single crystal.

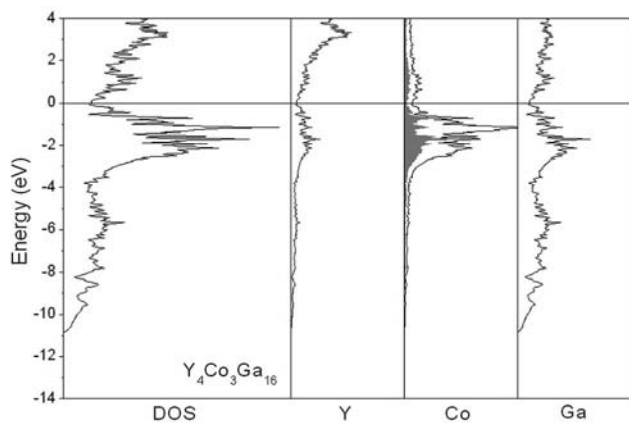
Electronic Structure

The electronic band structure was calculated for the non-magnetic representative Y₄Co₃Ga₁₆. The density of states (DOS) curve (Figure 6a) resembles that previously determined for Sm₄Co₃Ga₁₆,^[18] the Fermi level falls in a local minimum, consistent with the temperature-independent Pauli paramagnetism observed for Y₄Co₃Ga₁₆. The occurrence of mostly empty Y states, mostly filled Co states and partially filled Ga states agrees with the expected directions

of electron transfer from the Y atoms to the more electro-negative Co and Ga atoms. However, inspection of the crystal orbital Hamilton population (COHP) curves (Figure 6b) reveals that the bonding is far from ionic, given that the Y 5s/4d and Ga 4s/4p states mix over a wide energy range. Although these Y–Ga interactions are not strong (0.67 eV/bond), there are many of them because of the high CN12 coordination environments around the Y atoms. The most significant bonding contributions are the Co–Ga (2.4–2.5 Å, 1.88 eV/bond) and, to a lesser extent, the more distant Ga–Ga interactions (2.6–3.0 Å, 0.82 eV/bond). Interestingly, these Co–Ga and Ga–Ga interactions are precisely optimized, with bonding levels just completely occupied up to the Fermi level, a characteristic feature of Zintl phases. Notwithstanding the essentially identical Pauling electronegativities (1.8) of Co and Ga,^[20] the nearly electron-precise formulation (Y³⁺)₄(Co²⁺)₃(Ga^{1.1-})₁₆ allows the prediction of weak multicentre polyanionic Ga–Ga bonding. Although the filled Co 3d states are found in a fairly narrow energy range (down to −4 eV below the Fermi level), they do not represent localized electrons. A spin-polarized LMTO calculation (not shown) attempted on Y₄Co₃Ga₁₆ confirms that no magnetic moments develop on any atom; this result rules out the contribution of Co atoms to the effective magnetic moments of the other RE₄Co₃Ga₁₆ members.

Because the structure of RE₄Co₃Ga₁₆ is derived from the RE₂CoGa₈ host structure, which has to be distorted to accommodate the self-interstitial Co atoms into the centres of the octahedral Ga₆ clusters, it is of interest to determine how the bonding interactions evolve. A band structure calculation performed on Y₂CoGa₈ (Figure S4 in Supporting Information) reveals a DOS curve that is similar to that of Y₄Co₃Ga₁₆. The most important difference is that the inclusion of the octahedrally coordinated Co interstitial atoms, whose 3d states clearly separate into crystal-field split t_{2g} and e_g sets (shaded region in the Co projection shown in Figure 6a), augments the total Co–Ga bonding. Within the cubes of the PtHg₂-type slabs, the Co–Ga bonding is essentially unchanged on progressing from Y₂CoGa₈ (1.84 eV/bond) to Y₄Co₃Ga₁₆ (1.82 eV/bond), but within the octahedra of the AuCu₃-type slabs, the newly inserted Co atoms provide an additional contribution of 1.94 eV/bond. The distortion elongates some Ga–Ga distances but shortens others within the Ga square net in the AuCu₃-type slabs (Figure 3) such that the overall Ga–Ga bonding is also little changed in Y₂CoGa₈ (0.78 eV/bond) and Y₄Co₃Ga₁₆ (0.82 eV/bond). The development of these favourable Co–

(a)



(b)

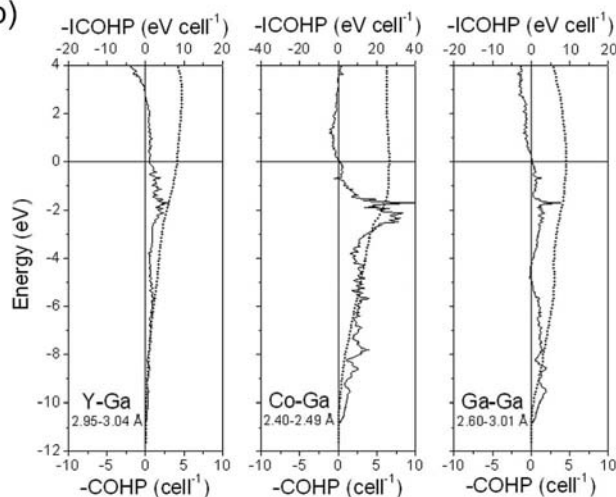


Figure 6. (a) Density of states (DOS) and its Y, Co and Ga projections for $\text{Y}_4\text{Co}_3\text{Ga}_{16}$. The shaded region in the Co projection highlights the contribution of the interstitial Co atoms centred within the octahedral Ga_6 clusters. (b) Crystal orbital Hamilton population (COHP) (solid line) and integrated COHP curves (dotted line) for Y–Ga, Co–Ga and Ga–Ga interactions. The horizontal lines at 0 eV mark the Fermi level.

Ga and Ga–Ga bonding interactions more than compensates for the weakening of the Y–Ga interactions (from 0.85 eV/bond in Y_2CoGa_8 to 0.67 eV/bond in $\text{Y}_4\text{Co}_3\text{Ga}_{16}$) as the Y-centred cuboctahedra distort to lower symmetry.

Conclusions

The preparation of $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ demonstrates that the available sites at the centres of octahedral Ga_6 clusters in the parent RE_2CoGa_8 compounds (Ho_2CoGa_8 -type structure) can be occupied by self-interstitial Co atoms, driven by a gain in additional Co–Ga bonding interactions. Structural considerations limit the extent of this series to the smaller RE atoms. It would be worthwhile to target the preparation of hypothetical $\text{RE}_4\text{M}_3\text{Ga}_{16}$ ($\text{M} = \text{Rh}, \text{Ir}$) or $\text{RE}_4\text{Co}_3\text{In}_{16}$ compounds to verify the factors limiting the substitutional range of RE. Analysis of the electronic structure suggests that, as in many other ternary RE–M–Ga

phases,^[24] electron transfer takes place from RE to both Co and Ga atoms, so that $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ contains formally anionic Co species as well as a polyanionic Ga–Ga network with weak multicentre bonding. The distortion accompanying the stuffing of Co atoms into RE_2CoGa_8 tends to be detrimental to the occurrence of interesting physical properties; the magnetic ordering temperatures decrease slightly and no superconducting transition was observed down to ca. 5 K in $\text{Tb}_4\text{Co}_3\text{Ga}_{16}$. This observation continues the trend previously made about the relationship between local structural distortions around the RE atoms and the occurrence of magnetic ordering in REMX_5 and RE_2MX_8 compounds.^[25]

Experimental Section

Synthesis: The starting materials were pieces of RE (Gd–Er, Y, 99.9%, Hefa), Co (99.5%, Aldrich) and Ga (99.99%, Cerac). These pieces were combined in stoichiometric proportions (4 RE + 3 Co + 16 Ga) and arc-melted in a Centorr 5TA tri-arc furnace or an Edmund Bühler MAM-1 compact arc melter on a water-cooled copper hearth under an argon atmosphere in the presence of a Ti getter. The alloys were melted, flipped over and remelted to ensure homogeneity; any weight loss was found to be less than 1%. The ingots were then sealed within evacuated fused-silica tubes and annealed at 800 °C for three weeks, followed by quenching in cold water. Attempts to extend the substitution to other RE metals (besides the previously known Sm member), both early and late, were unsuccessful under the same synthetic conditions.

Single crystals of the Gd and Tb members were obtained by combining excess Ga (0.3 g), which acts as a flux, with arc-melted ingots (0.3 g) prepared as described above and placed within fused-silica tubes, which were evacuated and sealed. The tubes were heated to 800 °C for two weeks, cooled to 500 °C over 48 h and then cooled to room temperature over 24 h. Black plate-shaped crystals were isolated from the Ga flux by sonication in warm ethanol, followed by filtration. Energy-dispersive X-ray (EDX) analysis of these crystals on a Hitachi S-2700 scanning electron microscope or a JEOL JSM 6700F field-emission scanning electron microscope revealed average compositions [atomic percentages of 19(2)% RE, 14(2)% Co and 67(2)% Ga] consistent with expectations (17% RE, 13% Co, 70% Ga). However, the uncertainties in this semiquantitative EDX analysis do not permit sufficient discrimination from related phases of similar composition, especially RECoGa_5 (14% RE, 14% Co, 71% Ga) and RE_2CoGa_8 (18% RE, 9% Co, 73% Ga). Moreover, these different phases crystallize with indistinguishable habits. The ultimate composition was established from the structure refinements described below. Extension of this crystal growth procedure to the other RE members ($\text{RE} = \text{Dy–Er}, \text{Y}$) yielded only crystals of RECoGa_5 and RE_2CoGa_8 when they were screened by single-crystal X-ray diffraction.

Structure Determination: Single-crystal X-ray diffraction data for $\text{RE}_4\text{Co}_3\text{Ga}_{16}$ ($\text{RE} = \text{Gd}, \text{Tb}$) were collected on a Bruker Platform/SMART 1000 CCD diffractometer at 22 °C by using ω scans (see Table 4). Structure solution and refinement were carried out with use of the SHELXTL (version 6.12) program package.^[26] Face-indexed numerical absorption corrections were applied. The centrosymmetric tetragonal space group $P4/mmm$ was chosen on the basis of intensity statistics and the isotropy with $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$.^[18] Initial atomic positions found by direct methods were consistent with $\text{Sm}_4\text{Co}_3\text{Ga}_{16}$; in particular, the interstitial Co2 atoms located at the

Table 4. Crystallographic data for RE₄Co₃Ga₁₆ (RE = Gd–Er, Y).^[a]

	Gd ₄ Co ₃ Ga ₁₆	Tb ₄ Co ₃ Ga ₁₆	Dy ₄ Co ₃ Ga ₁₆	Ho ₄ Co ₃ Ga ₁₆	Er ₄ Co ₃ Ga ₁₆	Y ₄ Co ₃ Ga ₁₆
Formula mass (amu)	1921.31	1927.99	1942.32	1952.03	1961.35	1647.99
<i>a</i> (Å)	6.0348(5)	6.0147(4)	5.9940(3)	5.9662(2)	5.9557(3)	6.0020(3)
<i>c</i> (Å)	11.1073(10)	11.0555(8)	11.0143(6)	10.9740(4)	10.9598(5)	11.0369(5)
<i>V</i> (Å ³)	404.51(6)	399.95(5)	395.73(3)	390.62(2)	388.75(3)	397.59(3)
$\rho_{\text{calcd.}}$ (g cm ⁻³)	7.887	8.005	8.150	8.298	8.378	6.883
Radiation	Mo- <i>K</i> _α	Mo- <i>K</i> _α	Cu- <i>K</i> _{α1}	Cu- <i>K</i> _{α1}	Cu- <i>K</i> _{α1}	Cu- <i>K</i> _{α1}
	$\lambda = 0.71073$ Å	$\lambda = 0.71073$ Å	$\lambda = 1.54051$ Å	$\lambda = 1.54051$ Å	$\lambda = 1.54051$ Å	$\lambda = 1.54051$ Å
μ (mm ⁻¹)	45.20	46.81	151.63	89.10	91.59	71.04
2θ range (°)	3.66–66.28	6.78–66.24	10.00–100.00	10.00–100.00	10.00–100.00	10.00–100.00
Refinement method	SHELXTL	SHELXTL	Rietveld	Rietveld	Rietveld	Rietveld
No. of data collected	5543	5554	3914	3914	3914	3914
No. of unique data	514 ($R_{\text{int}} = 0.052$)	512 ($R_{\text{int}} = 0.059$)	213 ^[b]	209 ^[b]	207 ^[b]	212 ^[b]
	[483 with $F_o^2 > 2\sigma(F_o^2)$]	[492 with $F_o^2 > 2\sigma(F_o^2)$]				
No. of variables	27	27	30	37	33	32
Residuals ^[c]	$R(F)$ [$F_o^2 > 2\sigma(F_o^2)$] = 0.024	$R(F)$ [$F_o^2 > 2\sigma(F_o^2)$] = 0.031	$R_B = 0.095$	$R_B = 0.092$	$R_B = 0.085$	$R_B = 0.100$
	$R_w(F_o^2) = 0.071$	$R_w(F_o^2) = 0.084$	$R_p = 0.021$	$R_p = 0.029$	$R_p = 0.041$	$R_p = 0.033$
			$R_{wp} = 0.028$	$R_{wp} = 0.047$	$R_{wp} = 0.056$	$R_{wp} = 0.046$

[a] Space group *P4/mmm* (No. 123); *Z* = 1. [b] Bragg reflections. [c] $R(F) = \Sigma||F_o| - |F_c||/\Sigma|F_o|$; $R_w(F_o^2) = \{\Sigma[w(F_o^2 - F_c^2)^2]/\Sigma w F_o^4\}^{1/2}$, $w^{-1} = [\sigma^2(F_o^2) + (A p)^2 + B p]$ where $p = [\max(F_o^2, 0) + 2F_c^2]/3$; $R_B = \Sigma|I_o - I_c|/\Sigma I_o$; $R_p = \Sigma|y_o - y_c|/\Sigma y_o$; $R_{wp} = [\Sigma w(y_o - y_c)]/\Sigma w y_o^{1/2}$.

origin were quite evident. Refinements proceeded in a straightforward manner; all sites were fully occupied with reasonable displacement parameters. Atomic positions were standardized with the program STRUCTURE TIDY.^[27] Further details on the crystal structure investigations may be obtained from the Fachinformationszentrum Karlsruhe, 76344 Eggenstein-Leopoldshafen, Germany (fax: +49-7247-808-666; e-mail: crysdata@fiz-karlsruhe.de), on quoting the depository number CSD-422805 (Gd₄Co₃Ga₁₆) and -422806 (Tb₄Co₃Ga₁₆).

Powder X-ray diffraction data for RE₄Co₃Ga₁₆ (RE = Dy, Ho, Er, Y) were collected with Cu-*K*_{α1} radiation on an Inel powder diffractometer equipped with a CPS 120 detector and were refined with the full-profile Rietveld method with use of the program FullProf (version 4.80).^[28] The least-squares refinements included scale factor, background, zero point, cell parameters, pseudo-Voigt peak profile parameters, atomic coordinates and isotropic displacement parameters. The displacement parameters were constrained to be equal for the two Co sites, and similarly for the four Ga sites. One reason for the relatively high R_B values is the likelihood that some RE₂CoGa₈ may be present as a minor impurity phase, as suggested by slight broadening of the peaks. All peaks in the powder diffraction pattern of RE₂CoGa₈ nearly overlap with those in RE₄Co₃Ga₁₆, which is distinguished mainly by the occurrence of additional weak superstructure peaks. However, the inability to resolve peaks belonging to RE₂CoGa₈ vs. RE₄Co₃Ga₁₆ (cf. $\sqrt{2}a = 5.97$ Å, $c = 10.99$ Å for Ho₂CoGa₈ vs. $a = 5.97$ Å, $c = 10.97$ Å for Ho₄Co₃Ga₁₆) causes the refinements to be unstable if both phases are included. Uncorrected absorption effects also influence the quality of the refinements.

Magnetic Susceptibility and Electrical Resistivity: Bulk samples of RE₄Co₃Ga₁₆ were difficult to prepare in high purity. As ascertained by powder X-ray diffraction, four samples (RE = Gd, Tb, Dy, Y) could be obtained in adequate purity (less than ca. 3% by mass of other phases; Figure S2 in Supporting Information), whereas the remaining two samples (RE = Ho, Er) were not sufficiently pure (>10% of other phases) to permit bulk magnetic measurements. Measurements of dc magnetic susceptibility were made under an applied field of 5000 Oe on a Quantum Design 9T-PPMS dc magnetometer. The susceptibility was corrected for contributions from the holder and underlying sample diamagnetism.

Electrical resistivity measurements were attempted on numerous single-crystal samples, but these efforts were thwarted by the impossibility in distinguishing between crystals of RE₄Co₃Ga₁₆ and RE₂CoGa₈ by visual inspection or EDX analyses alone. Selected crystals of Tb₄Co₃Ga₁₆ were the only ones that could be obtained in sufficiently large size (0.3 to 0.8 mm in length) and whose identities could be verified individually as the desired compound by single-crystal X-ray diffraction analysis. The electrical resistivity was measured by standard four-probe methods on a Quantum Design PPMS system equipped with an ac transport controller (Model 7100). The current was 100 μA, and the frequency was 16 Hz.

Band Structure Calculations: Tight-binding linear muffin tin orbital (TB-LMTO) band structure calculations were performed on Y₄Co₃Ga₁₆ within the local density and atomic spheres approximation with use of the Stuttgart TB-LMTO program.^[29] The basis sets consisted of Y 5s/5p/4d/4f, Co 4s/4p/3d and Ga 4s/4p/4d orbitals, and the Y 5p/4f and Ga 4d orbitals were downfolded. Integrations in reciprocal space were carried out with an improved tetrahedron method over 112 irreducible *k* points. For comparison, an analogous calculation was performed on Y₂CoGa₈, with atomic positions taken from the structure of Ho₂CoGa₈^[1] and integrations carried out over 220 irreducible *k* points.

Supporting Information (see also the footnote on the first page of this article): Rietveld refinement results, powder XRD patterns, additional magnetic data, and density of states (for a calculation on Y₂CoGa₈) are presented.

Acknowledgments

This work was supported by the Natural Sciences and Engineering Research Council of Canada. We thank Dr. Robert McDonald and Dr. Michael J. Ferguson (X-ray Crystallography Laboratory) for assistance with the single-crystal X-ray data collection and Ms. Christina Barker (Department of Chemical and Materials Engineering) and Ms. De-Ann Rollings (Department of Earth and Atmospheric Sciences) for the EDX analyses.

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Received: March 21, 2011

Published Online: June 17, 2011